

F Fuji Electric ht 6MBI150VB-060-50

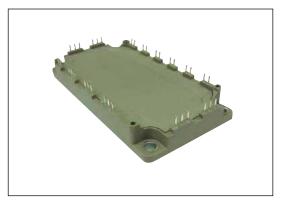
IGBT MODULE (V series) 600V / 150A / 6 in one package

Features

Compact Package P.C.Board Mount Low VCE (sat)

Applications

Inverter for Motor Drive AC and DC Servo Drive Amplifier Uninterruptible Power Supply Industrial machines, such as welding machines



Maximum Ratings and Characteristics

● Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

Items		Symbols	Conditions	Conditions		Units		
(Collector-Emitter voltage		Vces				V	
0	Gate-Emitter voltage		V _{GES}				V	
rter	Collector current		lc	Continuous	Tc=80°C	150		
۵ I			Іср	1ms	Tc=80°C	300	٨	
≦ '			-lc		· · · ·		A	
			-lc pulse	1ms	1ms			
(Collector power dissipation		Pc	1 device	1 device		W	
Junction temperature		Tj				°C		
Operating junciton temperature (under switching conditions)			Тјор					
Case temperature		Тс						
Storage temperature		Tstg						
sol	ation voltage	between terminal and copper base (*1) between thermistor and others (*2)	Viso	AC : 1min.	AC : 1min.		VAC	
Scr	ew torque	Mounting (*3)	-	M5	M5		N m	

Note *1: All terminals should be connected together during the test.

Note *2: Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

Note *3: Recommendable value : 2.5-3.5 Nm (M5)

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• Electrical characteristics (at Tj= 25°C unless otherwise specified)

4.0.		Sympole	Sumhala Canditiana			aracteris	tics	Units
tems		Symbols	Conditions		min.	typ.	max.	
	Zero gate voltage collector current	Ices	V _{GE} = 0V, V _{CE} = 600V		-	-	1.0	mA
	Gate-Emitter leakage current	Iges	$V_{GE} = 0V, V_{GE} = \pm 20V$		-	-	200	nA
	Gate-Emitter threshold voltage	V _{GE (th)}	V _{CE} = 20V, I _c = 150mA		6.2	6.7	7.2	V
	Collector-Emitter saturation voltage	V _{CE (sat)} (terminal)	V _{GE} = 15V I _c = 100A	Tj=25°C	-	2.45	2.90	- V
				Tj=125°C	-	2.75	-	
				Tj=150°C	-	2.95	-	
		V _{CE (sat)} (chip)	V _{GE} = 15V Ic = 150A	Tj=25°C	-	1.60	2.05	
				Tj=125°C	-	1.90	-	
				Tj=150°C	-	2.10	-	
H	Internal gate resistance	Rg(int)	-		-	6	-	Ω
	Input capacitance	Cies	V _{CE} = 10V, V _{GE} = 0V, f = 1MHz		-	9.7	-	nF
	Turn-on time	ton		-	0.36	1.20	μs	
Inverter		tr	Vcc = 300V	-	0.25	0.60		
		tr (i)	│Ic = 150A │Vge = +15 / -15V	-	0.07	-		
Ì	Town off these	toff	$R_{\rm g} = 9\Omega$	-	0.52	1.20		
	Turn-off time	tf		-	0.03	0.45		
Ì	Forward on voltage	V⊧ (terminal)		Tj=25°C	-	2.45	2.90	- V
			I⊧ = 150A	Tj=125°C	-	2.35	-	
		(terminal)		Tj=150°C	-	2.30	-	
			I⊧ = 150A	Tj=25°C	-	1.60	2.05	
		V⊧ (chip)		Tj=125°C	-	1.50	-	
				Tj=150°C	-	1.45	-	1
Ì	Reverse recovery time	trr	I _F = 150A		-	-	0.35	μs
5	Desistence	R	T = 25°C		-	5000	-	Ω
Thermistor	Resistance		T = 100°C		465	495	520	
1	B value	В	T = 25 / 50°C		3305	3375	3450	K

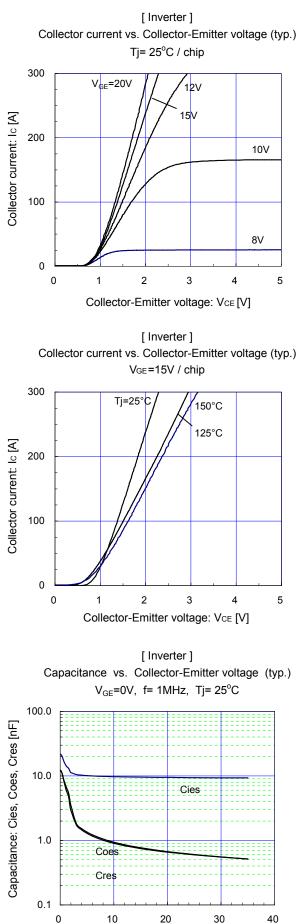
• Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
Items		Conditions	min.	typ.	max.	Units
"hormol reciptores (1 device)	Rth(j-c)	Inverter IGBT	-	-	0.31	°C/W
Thermal resistance (1device)		Inverter FWD	-	-	0.60	
Contact thermal resistance (1device) (*4)	Rth(c-f)	with Thermal Compound	-	0.05	-	

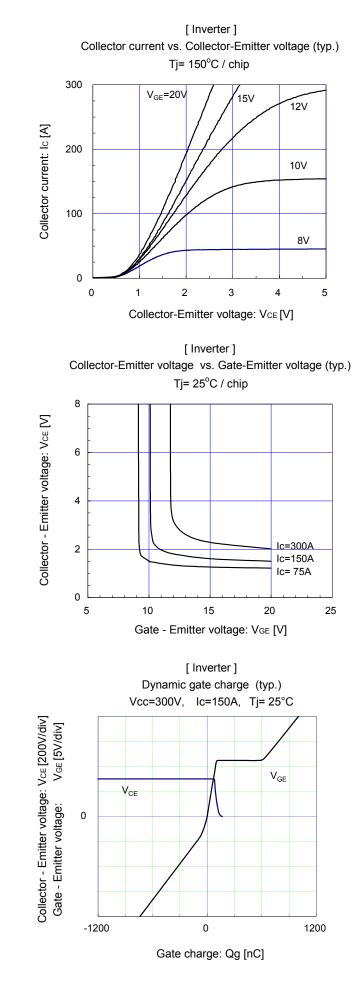
Note *4: This is the value which is defined mounting on the additional cooling fin with thermal compound.

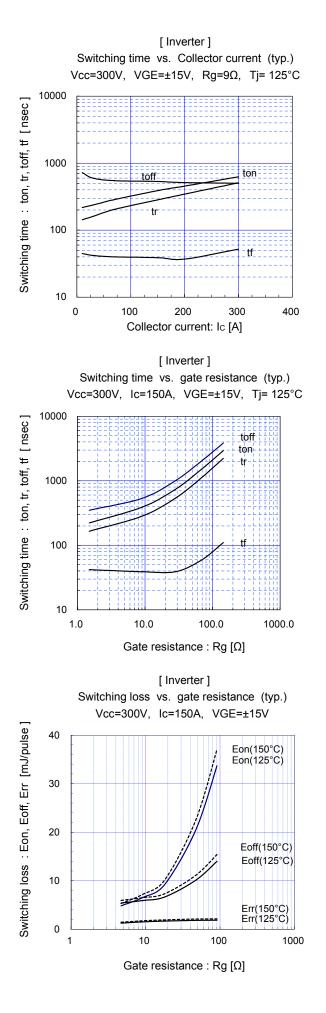
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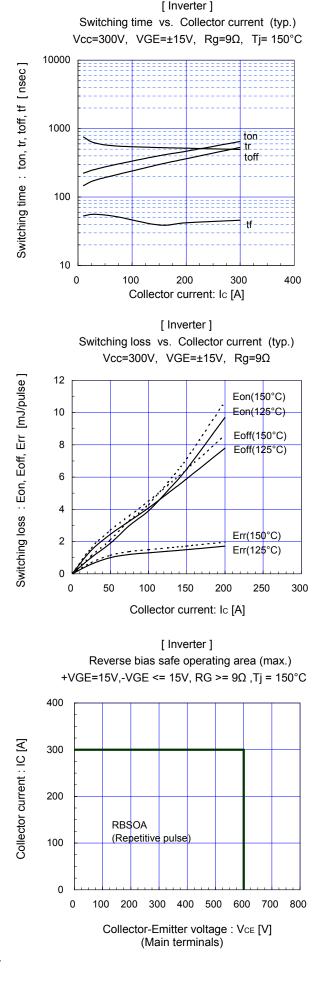
Characteristics (Representative)

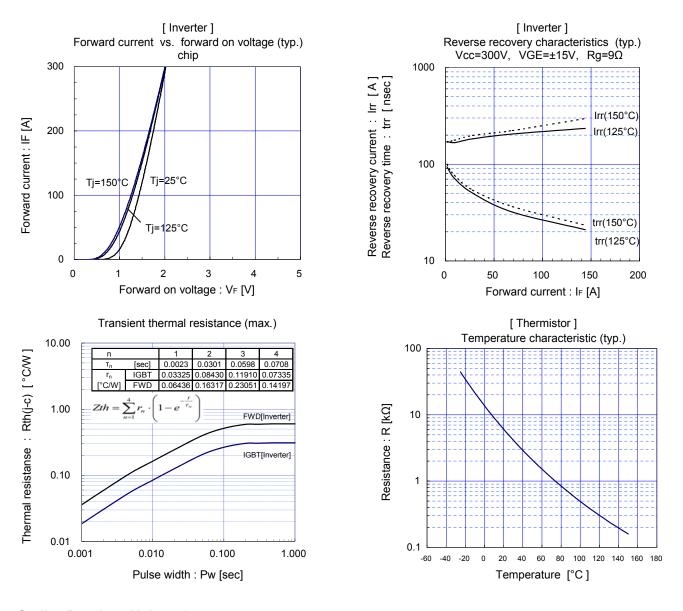


Collector - Emitter voltage: VCE [V]

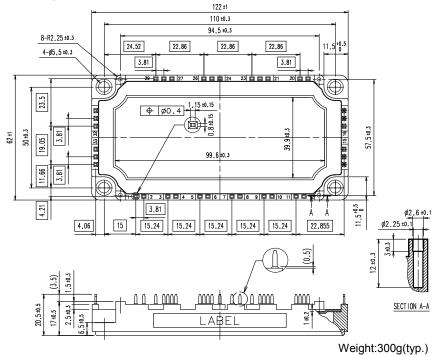












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Equivalent Circuit

